IMPERIAL COLLEGE LONDON

E4.06 A09 SO9 ISE4.36

DEPARTMENT OF ELECTRICAL AND ELECTRONIC ENGINEERING **EXAMINATIONS 2003** 

MSc and EEE/ISE PART IV: M.Eng. and ACGI

## **OPTICAL COMMUNICATION**

Tuesday, 20 May 10:00 am

Time allowed: 3:00 hours

There are SIX questions on this paper.

Answer Question ONE, and ANY THREE of Questions 2 to 6 All questions carry equal marks.

**Corrected Copy** 

Any special instructions for invigilators and information for candidates are on page 1.

Examiners responsible

First Marker(s):

E.M. Yeatman

Second Marker(s): K.D. Leaver



## Special instructions for invigilators: None.

## **Information for Candidates:**

Numbers in brackets in the right margin (e.g. [5]) indicate maximum marks for each section of each question.

The following constants may be used:

electron charge:

$$e = 1.6 \times 10^{-19} C$$

permittivity of free space:

$$\varepsilon_0 = 8.85 \text{ x } 10^{-12} \text{ F/m}$$

relative permittivity of silicon:

$$\varepsilon_r = 12$$

Planck's constant:

$$h = 6.63 \times 10^{-34} \text{ J s}$$

Boltzmann's constant:

$$k = 1.38 \times 10^{-23} \text{ J/K}$$

speed of light:

$$c = 3.0 \times 10^8 \text{ m/s}$$

The eigenvalue equations for TE modes in a symmetric slab waveguide of thickness d are

$$\kappa = k_{1x} tan(k_{1x} d/2)$$
 and  $\kappa = -k_{1x} cot(k_{1x} d/2)$ 

You should attempt all parts of this question. Short answers only are required; there is no need to re-state the questions in your answer book, but you should show any calculations you use to arrive at your answers, and give a brief (one or two lines) explanation where appropriate. All parts have equal value.

[20]

- a) A step index silica fibre has a core diameter of 6 μm and the cutoff wavelength for single mode operation is 1.520 μm. Estimate the index difference of the fibre.
- b) Raising the refractive index difference has what effect (if any) on the number of supported modes in step index multi-mode fibre?
- c) What loss mechanism dominates in silica-based fibre at wavelengths in the range 1600 2000 nm?
- d) Estimate the spread in wavelengths,  $\Delta\lambda$ , emitted by a light emitting diode at room temperature with a nominal operating wavelength of 1310 nm.
- e) Why is silicon not a suitable material for photodetectors for long-haul optical communication systems?
- Which of the following is currently the highest bit rate in commercial optical transmitters 10 Mbit/s, 400 Mbit/s, 1 Gbit/s, or 40 Gbit/s? What is the main factor limiting this value?
- g) Briefly explain the main performance advantage for optical communications of distributed feedback lasers over Fabry-Perot lasers.
- h) What is the maximum possible slope efficiency of a semiconductor laser operating at a nominal wavelength of 780 nm?
- i) Briefly describe the main considerations in choosing suitable wavelengths for pump lasers in erbium-doped fibre amplifiers.
- j) A passive 4-port coupler with negligible excess losses has an input of -10 dBm at one port, no signal at the other input port, and -20 dBm is emitted at one output port. What is the output power in dBm at the other output port and why?

2. a)	A symmetric slab waveguide has a core thickness of 6 $\mu$ m. For a certain transverse electric (TE) mode, the transverse wavevector component in the core is $k_{1x} = 1.19 \times 10^6$ m <sup>-1</sup> . Find the order m of this mode, and determine the total number of TE modes supported by this guide. You may find it helpful to sketch a graph of the eigenvalue equations.	[8]
b)	For the waveguide and mode of part (a), with a free-space wavelength of 1.50 $\mu$ m, the phase velocity is found to be $2.027 \times 10^8$ m/s. Find the refractive index of the core, n <sub>c</sub> , to 4 significant decimal places.	[6]
c)	For the waveguide and wavelength described in (a) and (b), estimate the effective index n', to 4 significant digits, of the lowest order (m=0) TE mode.	[6]
3. a)	Show that, at the wavelength $\lambda$ where $d^2n/d\lambda^2=0$ , the spread in pulse length due to material dispersion in a fibre is proportional to the third derivative of refractive index with respect to wavelength, i.e. $d^3n/d\lambda^3$ . Derive an expression for the pulse broadening $\Delta \tau_g$ in this case. Note that the group delay $\tau_g=(L/c)(n-\lambda dn/d\lambda)$ , where L is the fibre length.	[6]
b)	If the spread in wavelength of a signal is dominated by the inherent source width $\sigma_{\lambda S}$ , derive an expression for the received pulse width in the time domain $\sigma_R$ as a function of the transmitted pulse width $\sigma_o$ , the fibre length L, and the dispersion coefficient D.	

In a certain system the optical signal's spectral width is dominated by the input signal spectrum, and the inherent source width  $\sigma_{\lambda S}$  is negligible. The input pulses are transform limited Gaussian, with variance  $\sigma_0$ . Show that for a certain fibre dispersion D·L there is a minimum received pulse width  $\sigma_R$ . Find an expression for the input pulse width  $\sigma_0$  at which this is obtained, and for the corresponding pulse spreading ratio  $\sigma_R/\sigma_0$ .

Derive an expression for the minimum of  $\sigma_0$  as a function of  $\sigma_{\lambda S}$  for which the relative

[8]

[6]

pulse spreading  $\sigma_R/\sigma_o < 1.25$ .

- 4. a) A certain light emitting diode (LED) has radiative and non-radiative recombination lifetimes,  $\tau_{rr}$  and  $\tau_{nr}$  respectively, in the ratio  $\tau_{nr}/\tau_{rr}=5$ . Calculate the internal quantum efficiency for this device.
- [2]
- b) Describe four factors that may limit the external quantum efficiency in an LED, and for each of these indicate a technique that can reduce the effect of this factor.
- [8]
- c) An LED is emitting into a step index, silica-based multi-mode fibre as shown in Fig. 4.1. The numerical aperture of the fibre is 0.10. Find the maximum emission angle  $\theta$  from the LED active region for which light can be guided in the fibre, and the fraction of emitted power falling within this angle if the generated photons have a uniform directional distribution.

[6]

d) For the fibre described in (c), derive an expression for the limit on bit rate imposed by multi-mode dispersion, and sketch this as a function of fibre length.

[4]

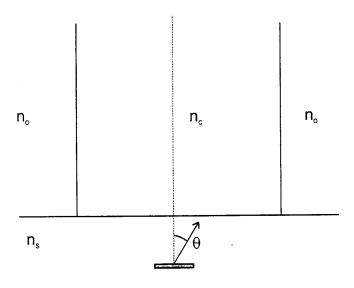


Figure 4.1

5.a) A certain receiver has unit quantum efficiency, and a noise equivalent power (NEP) of 5 pW/√Hz. Find the received optical power for which the shot noise and receiver noise are equal.

[4]

b) The receiver in (a) is used in a system with transmitted power of 10 mW, and fibre attenuation of 0.43 dB/km. On-off keying is used, the signal bandwidth is at the Nyquist limit, and the minimum optical SNR is 10 dB.

Find an expression for the maximum bit rate B as a function of fibre length L, and simplify this expression for the two cases where shot noise or receiver noise dominate respectively. Using these approximations, sketch log(B) vs. L over a practical range of fibre lengths.

[8]

c) The system described in part (a) is extended by adding an optical amplifier at a suitable point along the fibre. The amplifier has 20 dB gain and a noise figures of 4 dB. Modify your expressions from (b) for maximum bit rate, and sketch log(B) vs. L.

[8]

6. a) A silicon p-n photodiode (Fig. 6.1) has a depletion layer thickness of w, and p and n doping levels respectively of  $N_A$  and  $N_D$ , with  $N_A = 5N_D = 10^{20}$  m<sup>-3</sup>. The quantities  $w_p$  and  $w_n$  are the depleted widths in the p and n regions respectively. A reverse bias voltage  $V_b$  is applied. Find an expression for the full depletion width w as a function of  $V_b$ , and the value of  $V_b$  for which  $w = 10 \ \mu m$ .

[8]

b) Neglecting Fresnel reflection, find an expression for the quantum efficiency  $\eta$  of the photodiode of (a) if the total p region thickness  $h = 10 \mu m$ , and the absorption coefficient  $\alpha = 10^5 \text{ m}^{-1}$ . Hence find the value of  $V_b$  for which  $\eta = 0.9$ .

[6]

c) Assume that the resistance R encountered by the photocurrent I<sub>ph</sub> is dominated by the resistance of the undepleted part of the p region, as the current flows laterally through it as shown in Fig. 6.1. If this resistance is in turn is inversely proportional to the thickness h<sub>c</sub> of this region, find the value of h<sub>c</sub> in terms of h for which the time constant RC of the diode is minimised.

[6]

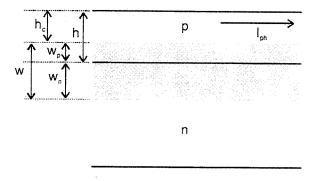


Figure 6.1

